

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Hyun Woo SONG, et al.

Serial No.: New Application Group Art Unit: Not Yet Assigned

Filed: March 16, 2004 Examiner: Not Yet Assigned

Title: METHOD FOR FABRICATING SEMICONDUCTOR OPTICAL DEVICE

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

March 16, 2004

Sir:

As a means of complying with the duty of disclosure under 37 CFR §1.56, and in accordance with 37 CFR §§1.97 and 1.98, Applicant(s), through the undersigned attorney, submits this Information Disclosure Statement. The patents, publications or other information submitted herewith are listed on the attached Form PTO-1449 and copies are attached.

In accordance with 37 CFR §1.97(b)(1) or (2), this Information Disclosure Statement is being filed either within three months of the filing date of the above-identified application, or within three months of the date of entry into the national stage of the above-identified application as set forth in 37 CFR §1.491. Accordingly, no fee is required.

Respectfully submitted,

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET NO.: P69577US0 GROUP ART UNIT: Not Yet Assigned
 SERIAL NO.: New Application FILING DATE: March 16, 2004
 APPLICANT(S): Hyun Woo SONG et al. TODAY'S DATE: March 16, 2004

 U.S. PATENT DOCUMENTS

*EXAMINER <u>INITIAL</u>	DOCUMENT <u>NUMBER</u>	DATE	NAME	INT'L <u>CLASS</u>	SUB- <u>CLASS</u>	FILING DATE <u>(If Appropriate)</u>
AA	<u>5,068,868</u>	<u>11/26/91</u>	<u>Deppe, et al.</u>	<u>H01S</u>	<u>3/19</u>	<u>5/21/90</u>
AB	<u>6,121,068</u>	<u>09/19/00</u>	<u>Ramdani, et al.</u>	<u>H01L</u>	<u>21/00</u>	<u>3/26/98</u>
AC	<u>5,711,811</u>	<u>1/27/98</u>	<u>Suntola et al.</u>	<u>C32C</u>	<u>16/00</u>	<u>11/28/95</u>

 FOREIGN PATENT DOCUMENTS

DOCUMENT <u>NUMBER</u>	DATE	COUNTRY	SUB- <u>CLASS</u>	TRANSLATION <u>(YES)</u> <u>(NO)</u>
AD	<u>11-307863</u>	<u>11/05/99</u>	<u>JAPAN</u>	<u>H01S</u> <u>3/18</u> <u>X</u>

 OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AE Chao-Kun Lin, et al; "Electrically pumped 1.3 VCSELs with InP/air-gap DBRs"; CLEO '02 Lasers and Electro-optics, 2002.; pp. 755-757.

AF C. AF Chao-Kun Lin, et al; "High temperature continuous-wave operation of 1.3-1.55 um VCSELs with InP/air-gap DBRs"; IEEE 18th International Semiconductor Laser Conference 2002; pp. 145-146.

AG I. Gaqnes, et al; "MOCVD InP/AlGaInAs distributed Bragg reflector for 1.55um VCSELs"; Electronics Letters 12th April 2001, Vol. 37, No. 8; pp. 500-501.

AH J.-H. Shin, et al; "CW Operation and Threshold Characteristics of All-Monolithic InAlGaAs 1.55-um VCSELs Grown by MOCVD"; IEEE Photonics Technology Letters, Vol. 14, No. 8; August 2002; pp. 1031-1033.

AI K. Streubel, et al; "1.26um vertical cavity laser with two InP/air-gap reflectors"; Electronics Letters 18th July 1996, Vol. 32, No. 15; pp. 1369-1370.

- AJ Hyun-Eoi SHIN, et al; "High-finesse $Al_xO_y/AlGaAs$ nonabsorbing optical cavity"; Applied Physics Letters; Vol. 72. No. 18; May 4, 1998; pp. 2205-2207.
- AH Sun Jin Yun, et al; "Dependence of atomic layer-deposited Al_2O_3 films characteristics on growth temperature and Al precursors of $Al(CH_3)_3$ and $AlCl_3$ "; J.Vac.Sci. Technol. A 15(6), Nov/Dec 1997; pp. 2993-2997.

EXAMINER

DATE CONSIDERED

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).